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CLMPTO

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Claims 1-29 (Cancelled)

Claim 30 (currently amended): A method of fabricating a semiconductor light emitting device, comprising the steps of:

forming a wurtzite-type compound semiconductor layer on a substrate oriented along a principal plane such that a difference-in-height portion is formed in a surface of the wurtzite-type compound semiconductor;

forming a crystal growth layer at least a portion of which is oriented along an inclined plane inclined with respect to the principal plane by crystal growth on the surface; and

applying a first conductive cladding layer, an active layer, and a second conductive layer in a stacked arrangement along a region extending in parallel to said inclined plane;

forming a first mask material layer, forming a first window region in the first mask material layer, and forming a first electrode layer through the first window region; and

forming a second mask material layer, forming a second window region in the second mask material layer at a position different from that of the first window region, and forming a second electrode layer through the second window region;

wherein one or more light emission regions having different characteristics are formed by using the first electrode layer and the second electrode layer.

Claim 31 (canceled)

Claim 32 (original): The method of claim 30, wherein the semiconductor light emitting device is separated into a plurality of light emission regions electrically independent from each other.

Claim 33 (original): The method claim 32, wherein an amount of current injected in the light emission regions is capable of being adjusted to establish wavelengths of light emitted from the light emission regions to a desired value.

Claim 34 (original): The method of claim 30 comprising the steps subsequent to the applying step of:

forming a resist layer, and forming a specific pattern of an electrode layer by a lift-off process.

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Claim 35 (original): The method of claim 30 comprising the steps subsequent to the applying step of:

forming a resist layer having a window region, forming an electrode layer to cover said resist layer including an inner region of said window region, and removing said resist layer together with said electrode layer excluding an electrode portion formed on a bottom region of the window region by a lift off process.

Claim 36 (original): The method of claim 30, wherein the crystal growth layer is grown at a temperature of about 1100°C or less.

Claim 37 (original): The method of claim 30, wherein the crystal growth layer is grown at a pressure of about 100 Torr or more.

Claims 38-44 (Cancelled)